



제 29회 한국반도체학술대회

The 29th Korean Conference on Semiconductors

2022년 1월 24일(월)~ 26일(수) | 강원도 하이원 그랜드호텔(컨벤션타워)

2022년 1월 25일(화), 16:00-17:45

Room D (사파이어 II+III, 5층)

K. Memory (Design & Process Technology) 분과

[TD3-K] RRAM II

좌장: 곽준영 박사(KIST), 강대웅 담당(SK 하이닉스)

<p>TD3-K-1 16:00-16:15</p>	<p>Demonstration of Sneak Current-Based A* Pathfinding Algorithm Yoon Ho Jang, Janguk Han, and Cheol Seong Hwang <i>Department of Materials Science and Engineering and Inter-University Semiconductor Research Center, Seoul National University</i></p>
<p>TD3-K-2 16:15-16:30</p>	<p>Reversible Multi-mode Synaptic Operation of HfAlO_x-Based Memristor for Neuromorphic Application Hyung Seok Shin, Hanchan Song, Do Hoon Kim, Alba Martinez, Woon Hyung Cheong, and Kyung Min Kim <i>KAIST</i></p>
<p>TD3-K-3 16:30-16:45</p>	<p>Coexistence of Oxygen Vacancy and Metallic Silver Electrochemically Filament Formation in ZrO₂ Based Memory Devices Jamal Aziz^{1,2} Honggyun Kim^{1,2}, and Deok-kee Kim^{1,2} <i>¹Department of Electrical Engineering, Sejong University, ²Department of Convergence Engineering for Intelligent Drone, Sejong University</i></p>
<p>TD3-K-4 16:45-17:00</p>	<p>Non-Volatile RRAM based on Single-layer hBN for Artificial Synapse Yooyeon Jo, Eunpyo Park, Gichang Noh, Jongkil Park, Jaewook Kim, Yeon Joo Jeong, Suyoun Lee, Inho Kim, Jong-Keuk Park, and Joon Young Kwak <i>KIST</i></p>
<p>TD3-K-5 17:00-17:15</p>	<p>Highly Reliable Artificial Synapse based on Two-dimensional Material - Oxide Bilayer Memristor Wonbae Ahn, Jun-Hwe Cha, Jungyeop Oh, Sanggeun Bae, and Sung-Yool Choi <i>School of Electrical Engineering, Graphene/2D Materials Research Center, Center for Advanced Materials Discovery towards 3D Displays, KAIST</i></p>
<p>TD3-K-6 17:15-17:30</p>	<p>Bipolar Gradual Resistive Switching of a Simple a-InGaZnO₄ Based Memristor Haripriya G. R., Hee Yeon Noh, Myoung-Jae Lee, and Hyeon-Jun Lee <i>Division of Nanotechnology, DGIST</i></p>
<p>TD3-K-7 17:30-17:45</p>	<p>Theoretical Analysis on the Stochastic Oscillation near NDR-2 in NbO_x-Based Threshold Switching Nano-electronic Device Hakseung Rhee, Gwangmin Kim, Jae Hyun In, Woojoon Park, Hanchan Song, and Kyung Min Kim <i>Department of Materials Science and Engineering, KAIST</i></p>